

ABSTRACT OF THE DISCLOSURE

A gate-insulated thin film transistor is disclosed. One improvement is that the thin film transistor is formed on a substrate through a blocking layer in between so that it is possible to prevent the transistor from being contaminated with impurities such as alkali ions which exist in the substrate. Also, a halogen is added to either or both of the blocking layer and a gate insulator of the transistor in order that impurities such as alkaline ions, dangling bonds and the like can be neutralized, therefore, the reliability of the device is improved.